Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

- Small Size Surface Mount DPAK Package
- Passivated Die for Reliability and Uniformity
- Four-Quadrant Triggering
- Blocking Voltage to 600 V
- On–State Current Rating of 4.0 Amperes RMS at 93°C
- Low Level Triggering and Holding Characteristics
- Device Marking: Device Type with "M" truncated, e.g., MAC4DLM: AC4DLM, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (1) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	V _{DRM,} V _{RRM}		Volts
MAC4DLM		600	
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 93°C)	IT(RMS)	4.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _J = 110°C)	ITSM	40	Amps
Circuit Fusing Consideration (t = 8.3 msec)	I ² t	6.6	A ² sec
Peak Gate Power (Pulse Width ≤ 10 μsec, T _C = 93°C)	PGM	0.5	Watts
Average Gate Power (t = 8.3 msec, T _C = 93°C)	P _G (AV)	0.1	Watts
Peak Gate Current (Pulse Width ≤ 10 μsec, T _C = 93°C)	I _{GM}	0.2	Amps
Peak Gate Voltage (Pulse Width ≤ 10 μsec, T _C = 93°C)	VGМ	5.0	Volts
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C

⁽¹⁾ V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.



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TRIACS 4.0 AMPERES RMS 600 VOLTS





CASE 369

STYLE 6



D-PAK CASE 369A STYLE 6

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

ORDERING INFORMATION

Device	Package	Shipping
MAC4DLMT4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)
MAC4DLM-1	DPAK 369	75 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance — Junction to Case — Junction to Ambient — Junction to Ambient (1)	R _θ JC R _θ JA R _θ JA	3.5 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (2)	TL	260	°C

⁽¹⁾ Surface mounted on minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Peak Repetitive Blocking Current (V_D = Rated V_{DRM} , V_{RRM} ; Gate Open) $T_J = 25^{\circ}C$ $T_J = 110^{\circ}C$	I _{DRM,} I _{RRM}	_	=	0.01 2.0	mA		
ON CHARACTERISTICS	-	<u> </u>	•		-		
Peak On–State Voltage ⁽¹⁾ (I _{TM} = ±6.0 A)	VTM	_	1.3	1.6	Volts		
Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	^I GT	 - - -	1.8 2.1 2.4 4.2	3.0 3.0 3.0 5.0	mA		
Gate Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	VGT	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	Volts		
Gate Non–Trigger Voltage (V _D = 12 V, R _L = 100 Ω , T _J = 110°C) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-); MT2(-), G(+)	V _{GD}	0.1	0.4	_	Volts		
Holding Current (V _D = 12 V, Gate Open, Initiating Current = ±200 mA)	lн	_	1.5	15	mA		
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	lι	_ _ _ _	1.75 5.2 2.1 2.2	10 10 10 10	mA		

DYNAMIC CHARACTERISTICS

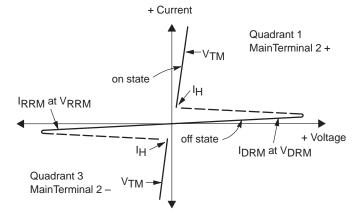
Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current $(V_D=200~V,~I_{TM}=1.8~A,~Commutating~dv/dt=1.0~V/\mu sec,~T_J=110^{\circ}C,~f=250~Hz,~CL=5.0~\mu fd,~LL=80~mH,~RS=56~\Omega,~CS=0.03~\mu fd)~With~snubber~see~Figure~11$	di/dt(c)		3.0	_	A/ms
Critical Rate of Rise of Off–State Voltage (V _D = 0.67 X Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 110°C)	dv/dt	10	_	_	V/μs

⁽¹⁾ Pulse Test: Pulse Width ≤ 2.0 msec, Duty Cycle ≤ 2%.

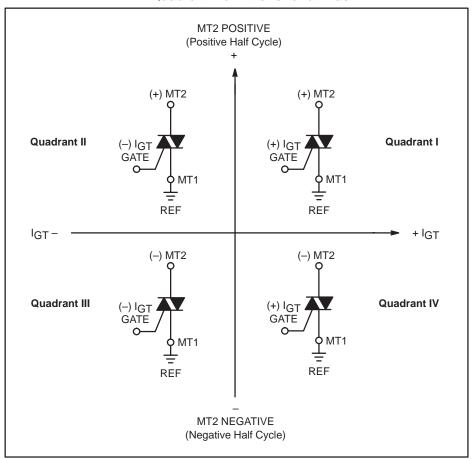
^{(2) 1/8&}quot; from case for 10 seconds.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
lΗ	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

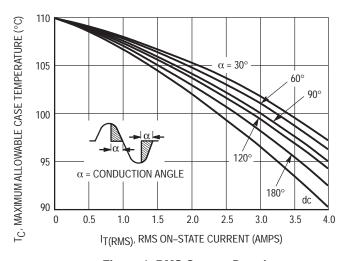


Figure 1. RMS Current Derating

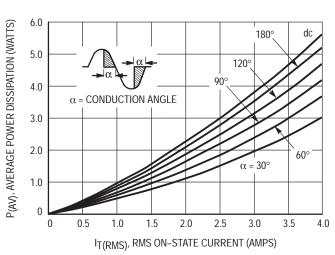


Figure 2. On-State Power Dissipation

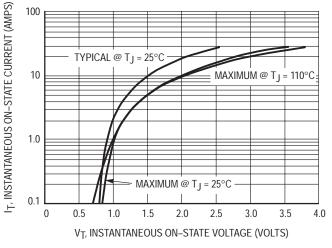


Figure 3. On-State Characteristics

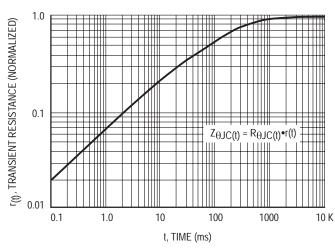


Figure 4. Transient Thermal Response

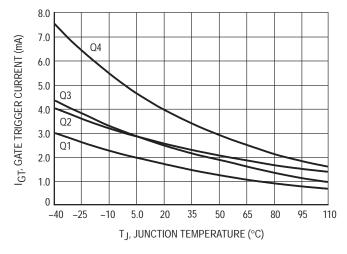


Figure 5. Typical Gate Trigger Current versus
Junction Temperature

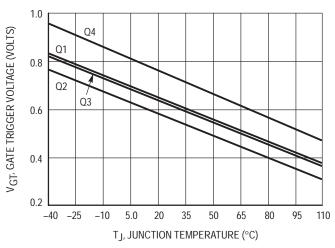
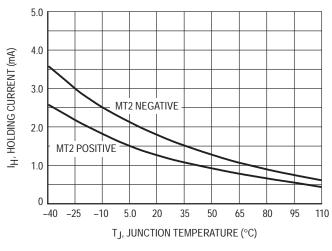


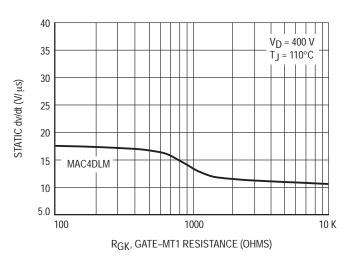
Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature



12 10 IL, LATCHING CURRENT (mA) 8.0 Q2 6.0 4.0 2.0 0 -40 -25 -10 5.0 95 20 35 50 65 80 110 T J, JUNCTION TEMPERATURE (°C)

Figure 7. Typical Holding Current versus Junction Temperature

Figure 8. Typical Latching Current versus Junction Temperature



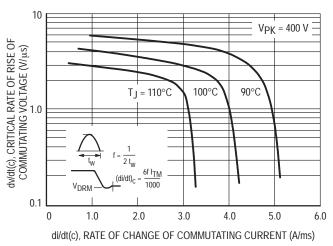
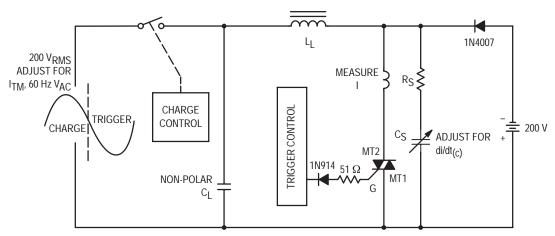


Figure 9. Minimum Exponential Static dv/dt versus Gate-MT1 Resistance

Figure 10. Critical Rate of Rise of Commutating Voltage



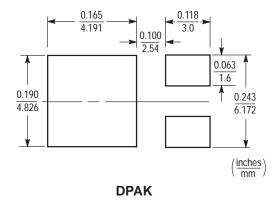
Note: Component values are for verification of rated (di/dt)_C. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)_C

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

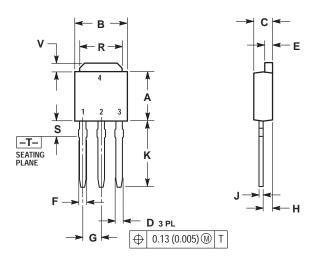
Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



PACKAGE DIMENSIONS

D-PAK CASE 369-07 ISSUE L



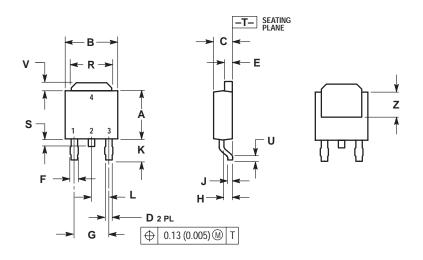
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.250	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
E	0.033	0.040	0.84	1.01	
F	0.037	0.047	0.94	1.19	
G	0.090 BSC		2.29 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.350	0.380	8.89	9.65	
R	0.175	0.215	4.45	5.46	
S	0.050	0.090	1.27	2.28	
V	0.030	0.050	0.77	1 27	

STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

D-PAK CASE 369A-13 ISSUE Z



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.250	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
E	0.033	0.040	0.84	1.01	
F	0.037	0.047	0.94	1.19	
G	0.180 BSC		4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.090 BSC		2.29 BSC		
R	0.175	0.215	4.45	5.46	
S	0.020	0.050	0.51	1.27	
U	0.020		0.51		
٧	0.030	0.050	0.77	1.27	
Z	0.138		3.51		

STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

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